- P12.9 (a) This NMOS transistor is operating in saturation because we have  $v_{GS} \ge V_{to}$  and  $v_{DS} \ge v_{GS} V_{to}$ . Thus,  $I_a = K(v_{GS} V_{to})^2 = 1.8 \text{ mA}$ .
  - (b) This PMOS transistor is operating in saturation because we have  $v_{GS} \le V_{to}$  and  $v_{DS} = -4 \le v_{GS} V_{to} = -3 (-1) = -2$ . Thus,  $I_b = K(v_{GS} V_{to})^2 = 0.8$  mA.
  - (c) This PMOS transistor is operating in the triode region because we have  $v_{\mathcal{GS}} \leq V_{to}$  and  $v_{DS} = -1 \geq v_{\mathcal{GS}} V_{to} = -5 (-1) = -4$ . Thus,  $I_c = K[2(v_{\mathcal{GS}} V_{to})v_{DS} v_{DS}^2] = 1.4 \text{ mA}$ .
  - (d) This NMOS transistor is operating in the triode region because we have  $v_{\mathcal{GS}} \geq V_{to}$  and  $v_{\mathcal{DS}} = 1 \leq v_{\mathcal{GS}} V_{to} = 3 1 = 2$ . Thus,  $I_d = K[2(v_{\mathcal{GS}} V_{to})v_{\mathcal{DS}} v_{\mathcal{DS}}^2] = 0.6$  mA.
- P12.13

$$i_D=k(V_{GS}-V_{t0})^2$$

$$0.8 = 0.2(V_{GS}+1)^2$$

P12.31\* We can write  $V_{DD} = V_{DSQ} + R_S I_{DQ}$ . Substituting values and solving, we obtain  $R_S = 3 \text{ k}\Omega$ . Next we have  $K = \frac{1}{2} \text{KP}(W/L) = 2 \text{ mA/V}^2$ . Assuming that the NMOS operates in saturation, we have

Substituting values and solving, we find  $V_{\mathcal{GSQ}}=0$  V and  $V_{\mathcal{GSQ}}=2$  V. The correct root is  $V_{\mathcal{GSQ}}=2$  V. (As a check we see that the device does operate in saturation because we have greater than ) Then we have  $V_{\mathcal{G}}=V_{\mathcal{GSQ}}+R_{\mathcal{S}}I_{\mathcal{DQ}}=8$  V. However we also have

Substituting values and solving, we obtain  $R_2 = 2 \text{ M}\Omega$ .

P12.33 We have  $V_G = V_{GSQ} = 5R_2/(R_1 + R_2) = 2.5$  V. Then we have  $I_{DQ} = K(V_{GSQ} - V_{to})^2 = 1.28$  mA.  $V_{DSQ} = V_{DD} - R_D I_{DQ} = -0.12$  V. For the MOSFET to operate in saturation  $R_D$  cannot exceed 2.65  $k\Omega$ 

P12.53\* (a) 
$$V_{\mathcal{G}} = V_{DD} \frac{R_2}{R_1 + R_2} = 20 \frac{0.3}{1.7 + 0.3} = 3 \text{ V}$$

$$V_{\mathcal{GSQ}} = V_{\mathcal{G}} = 3 \text{ V}$$

$$K = \frac{1}{2} KP(W / L) = 2.5 \text{ mA/V}^2$$

$$I_{DQ} = K(V_{\mathcal{GSQ}} - V_{to})^2 = 10 \text{ mA}$$

$$V_{DSQ} = V_{DD} - R_D I_{DSQ} = 10 \text{ V}$$

$$g_m = 2 \sqrt{KI_{DQ}} = 0.01 \text{ S}$$

(b) 
$$R'_{L} = \frac{1}{1/R_{D} + 1/R_{L}} = 500 \Omega$$
  
 $A_{V} = -g_{m}R'_{L} = -5$   
 $R'_{in} = \frac{1}{1/R_{1} + 1/R_{2}} = 255 \text{ k}\Omega$   
 $R_{o} = R_{D} = 1 \text{ k}\Omega$ 

## P12.62

